

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS™ C6 700V

700V CoolMOS™ C6 Power Transistor  
SS05N70

## Data Sheet

Rev. 2.0

Final

Industrial & Multimarket

## 1 Description

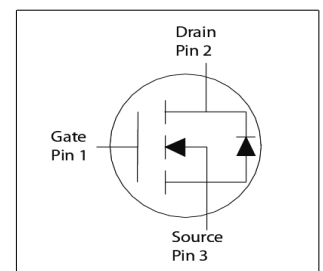
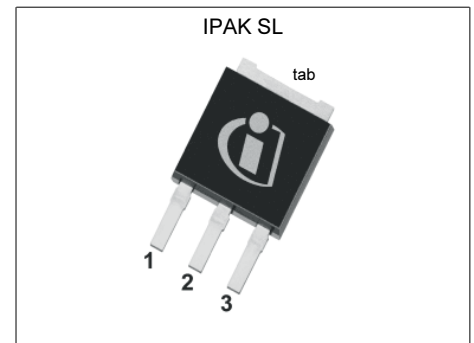
CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

## Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for consumer grade applications according to JEDEC (J-STD20 and JESD22)

## Applications

Adapter, LCD & PDP TV



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j\max}$	750	V
$R_{DS(on),\max}$	1.4	$\Omega$
$Q_g, \text{typ}$	10.5	nC
$I_D, \text{pulse}$	8.3	A
$E_{oss} @ 400V$	1.15	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
SS05N70	PG-TO 251	SS05N70	see Appendix A

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## 2 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$			3.2	A	$T_C = 25^\circ\text{C}$
				2.0		$T_C = 100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$			8.3	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$			26	mJ	$I_D = 0.6\text{A}$ , $V_{DD} = 50\text{V}$ (see table 18)
Avalanche energy, repetitive	$E_{AR}$			0.10	mJ	$I_D = 0.6\text{A}$ , $V_{DD} = 50\text{V}$
Avalanche current, repetitive	$I_{AR}$			0.6	A	
MOSFET dv/dt ruggedness	dv/dt			50	V/ns	$V_{DS} = 0 \dots 480\text{V}$
Gate source voltage	$V_{GS}$	-20		20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Operating and storage temperature	$T_j, T_{stg}$	-55		150	$^\circ\text{C}$	
Continuous diode forward current	$I_S$			2.8	A	$T_C = 25^\circ\text{C}$
Diode pulse current	$I_{S,pulse}$			8.3	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt			15	V/ns	$V_{DS} = 0 \dots 400\text{V}$ , $I_{SD} \leq I_D$ , $T_j = 25^\circ\text{C}$ (see table 16)
Maximum diode commutation speed	di/dt			500	A/ $\mu\text{s}$	
Power dissipation	$P_{tot}$			28	W	$T_C = 25^\circ\text{C}$

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum duty cycle  $D=0.75$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics IPAK SL**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$			4.4	°C/W	
Thermal resistance, junction - ambient <sup>1)</sup>	$R_{thJA}$			62	°C/W	leaded
			35			SMD version, device on PCB, 6cm <sup>2</sup> cooling area
Soldering temperature, wave- & reflowsoldering allowed	$T_{sold}$			260	°C	1.6 mm (0.063 in.) from case for 10s

<sup>1)</sup> Device on 40mm\*40mm\*1.5mm one layer epoxy PCB FR4 with 6cm<sup>2</sup> copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	700			V	$V_{GS} = 0V, I_D = 1mA$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5	V	$V_{DS} = V_{GS}, I_D = 0.10mA$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu A$	$V_{DS} = 700V, V_{GS} = 0V, T_j = 25^\circ C$
			10			$V_{DS} = 700V, V_{GS} = 0V, T_j = 150^\circ C$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS} = 20V, V_{DS} = 0V$
Drain-source on-state resistance	$R_{DS(on)}$		1.26	1.4	$\Omega$	$V_{GS} = 10V, I_D = 1.0A, T_j = 25^\circ C$
			3.28			$V_{GS} = 10V, I_D = 1.0A, T_j = 150^\circ C$
Gate resistance	$R_G$		6.5		$\Omega$	$f = 1MHz$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$		225		pF	$V_{GS} = 0V, V_{DS} = 100V, f = 1MHz$
Output capacitance	$C_{oss}$		18		pF	
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$		10		pF	$V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$		42		pF	$I_D = \text{constant}, V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Turn-on delay time	$t_{d(on)}$		7.7		ns	$V_{DD} = 400V, V_{GS} = 13V, I_D = 1.5A, R_G = 10.2\Omega$ (see table 17)
Rise time	$t_r$		5.9		ns	
Turn-off delay time	$t_{d(off)}$		33		ns	
Fall time	$t_f$		18.2		ns	

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$		1.3		nC	$V_{DD} = 480V, I_D = 1.5A, V_{GS} = 0 \text{ to } 10V$
Gate to drain charge	$Q_{gd}$		5.8		nC	
Gate charge total	$Q_g$		10.5		nC	
Gate plateau voltage	$V_{plateau}$		5.4		V	

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 480V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 480V

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$		0.9		V	$V_{GS} = 0V, I_F = 1.5A, T_j = 25^\circ C$
Reverse recovery time	$t_{rr}$		200		ns	$V_R = 400V, I_F = 1.5A,$ $di_F/dt = 100A/\mu s$ (see table 16)
Reverse recovery charge	$Q_{rr}$		0.9		$\mu C$	
Peak reverse recovery current	$I_{rrm}$		8		A	

## 5 Electrical characteristics diagrams

Table 8

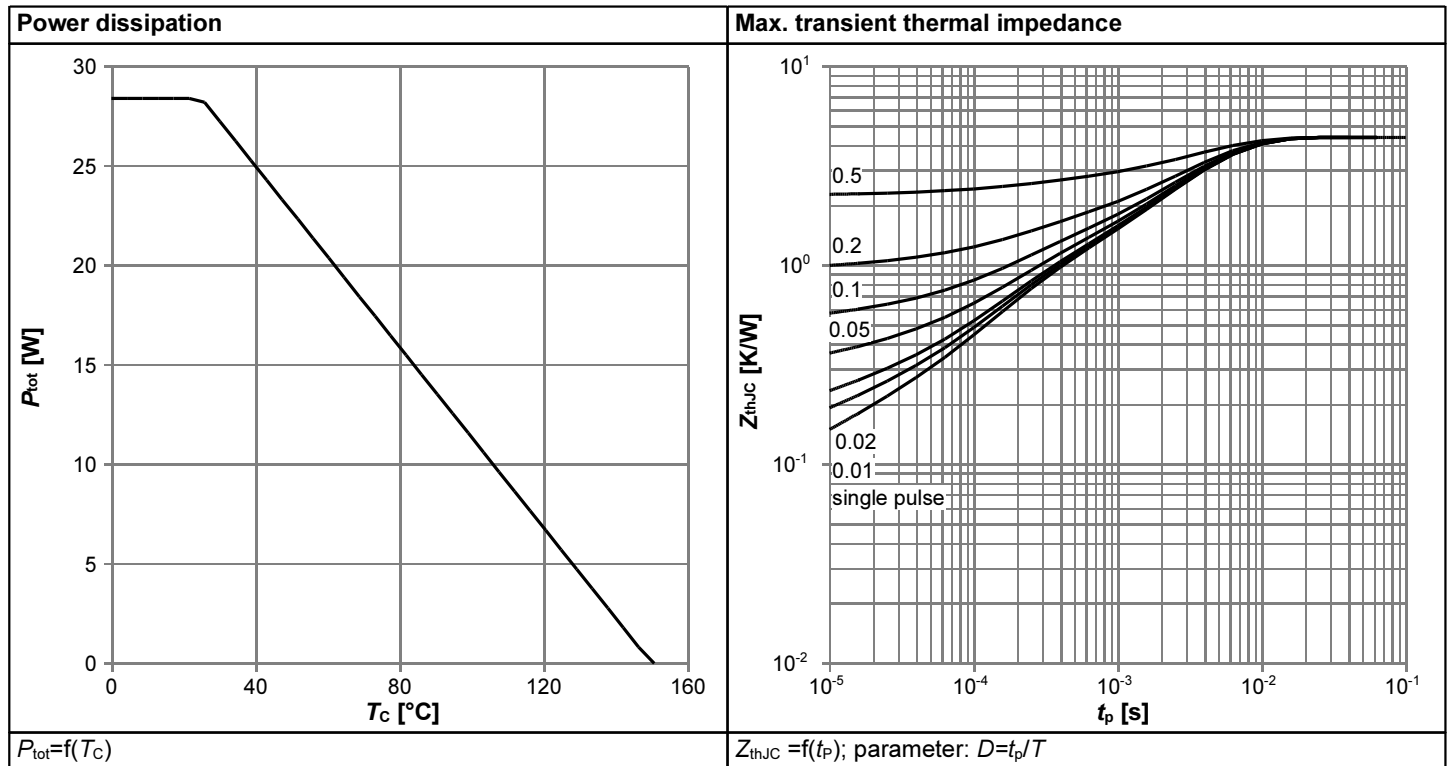


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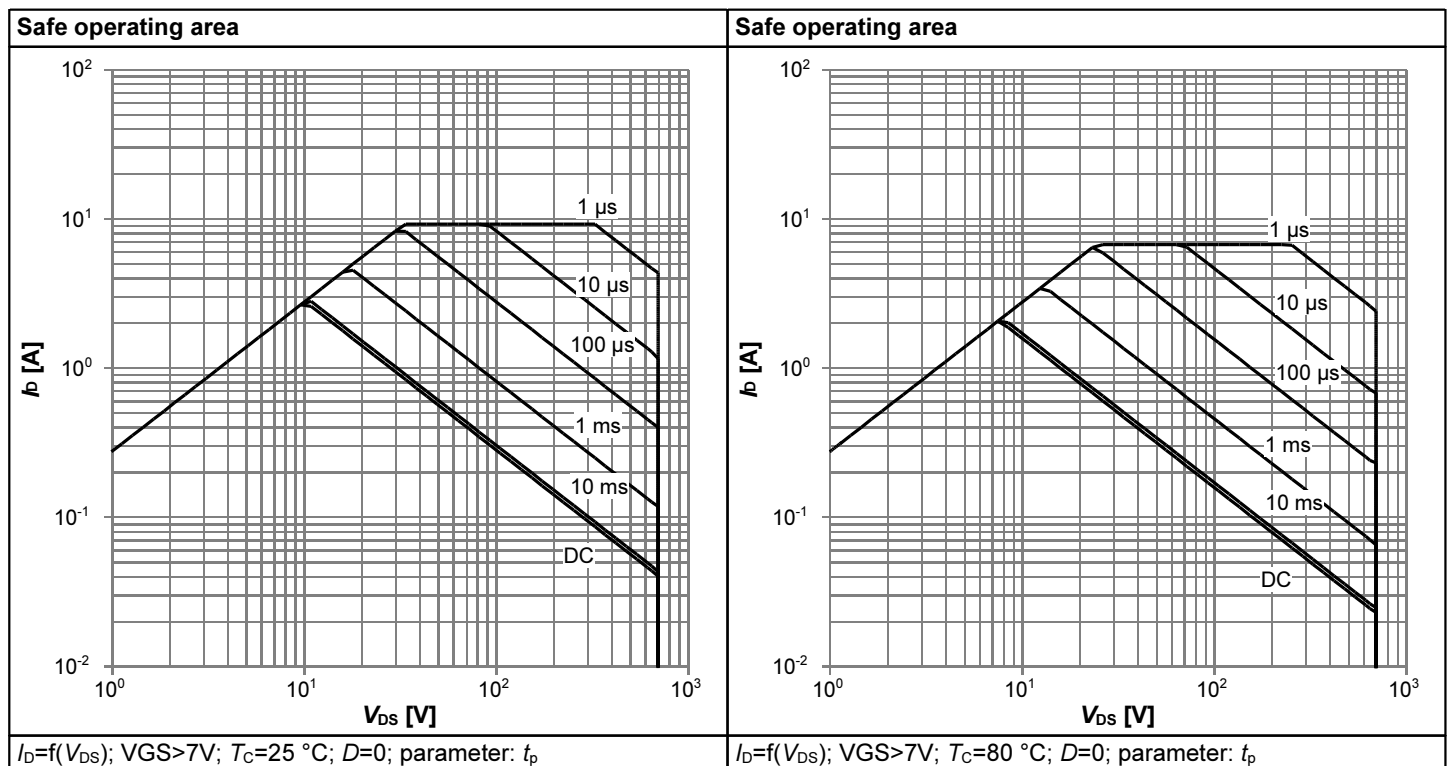




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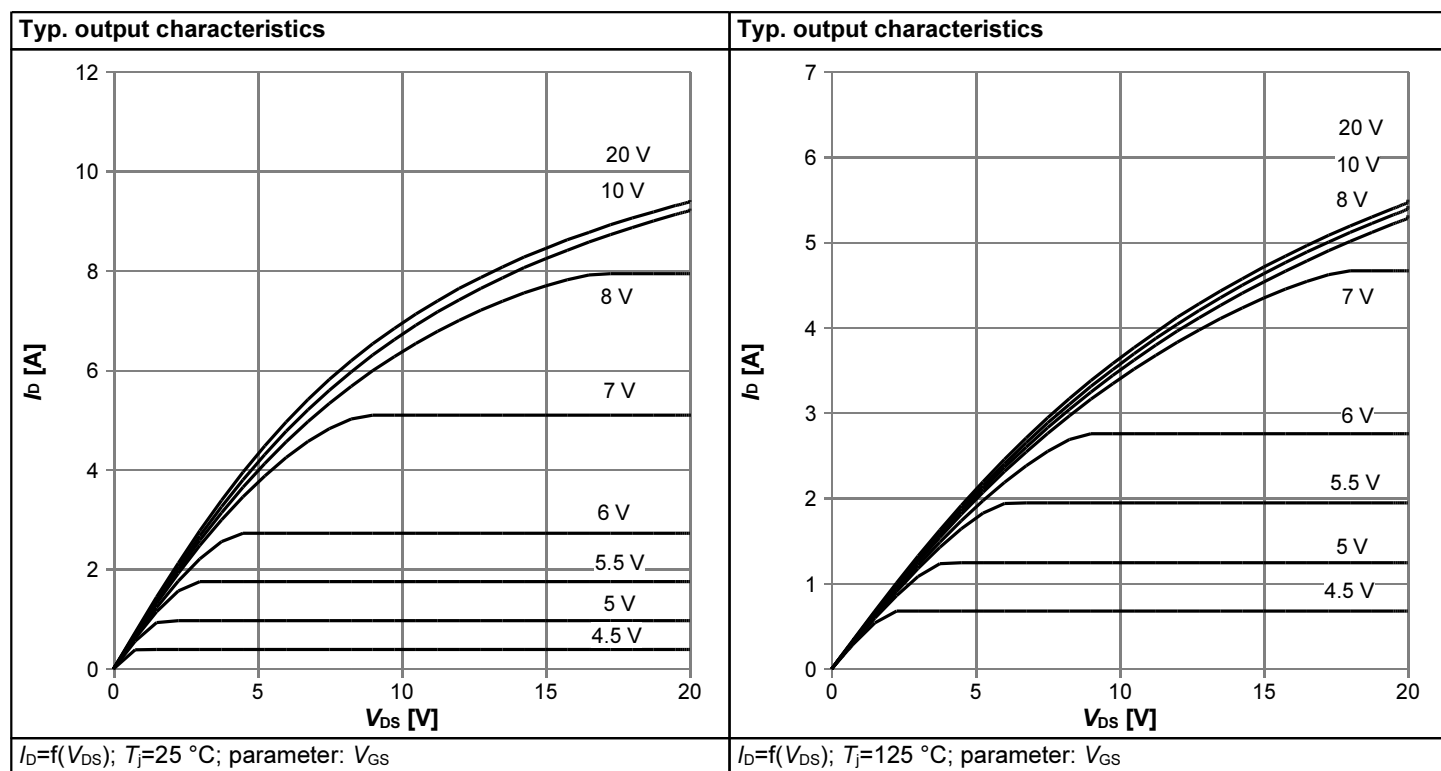


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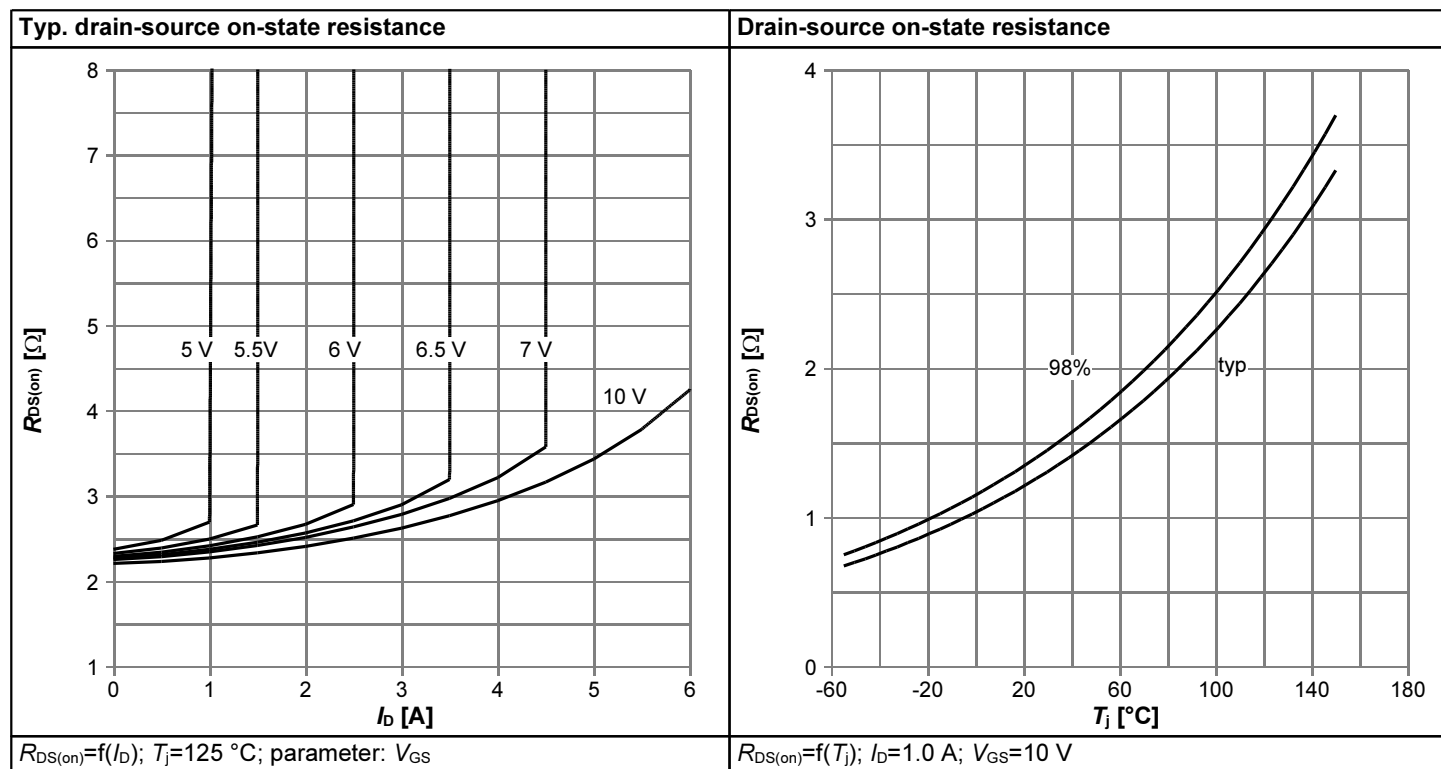


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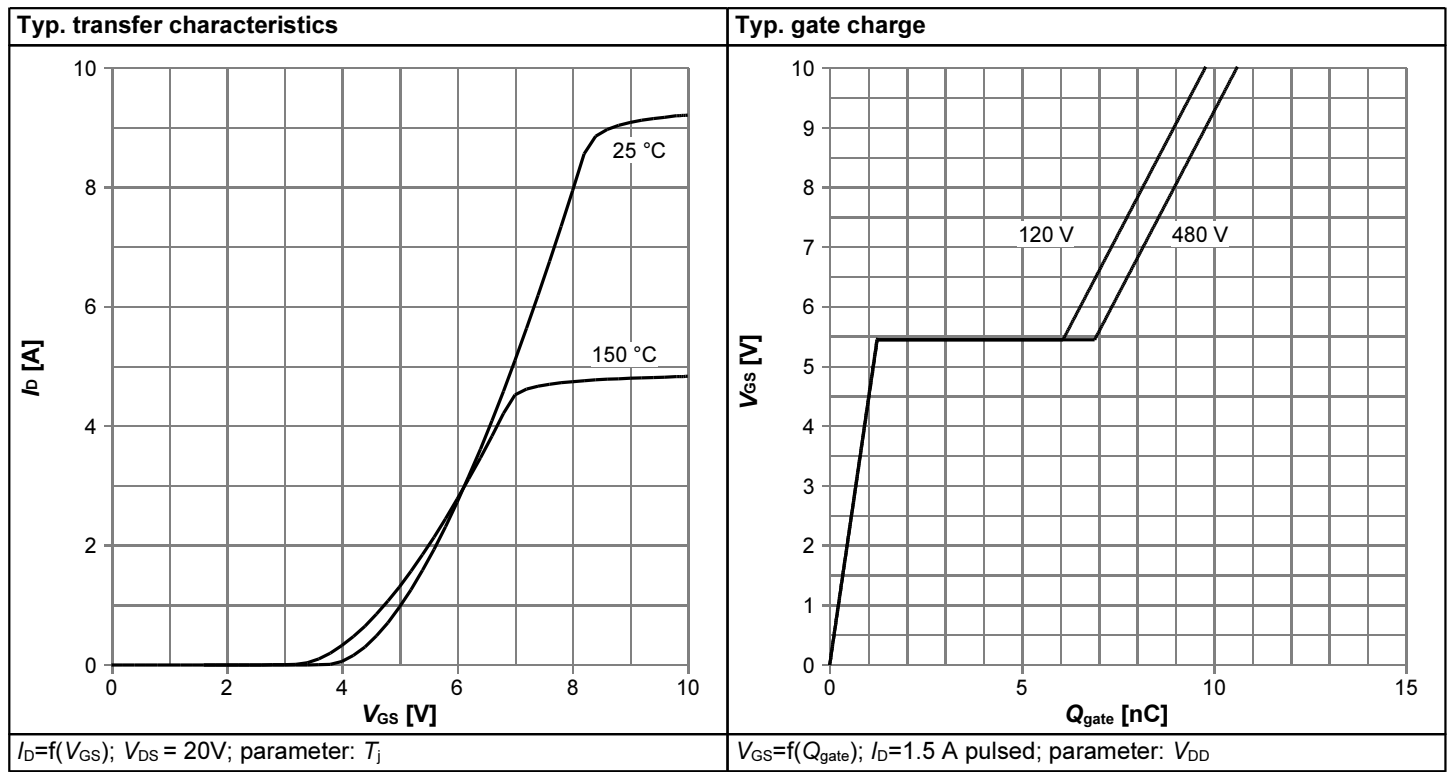


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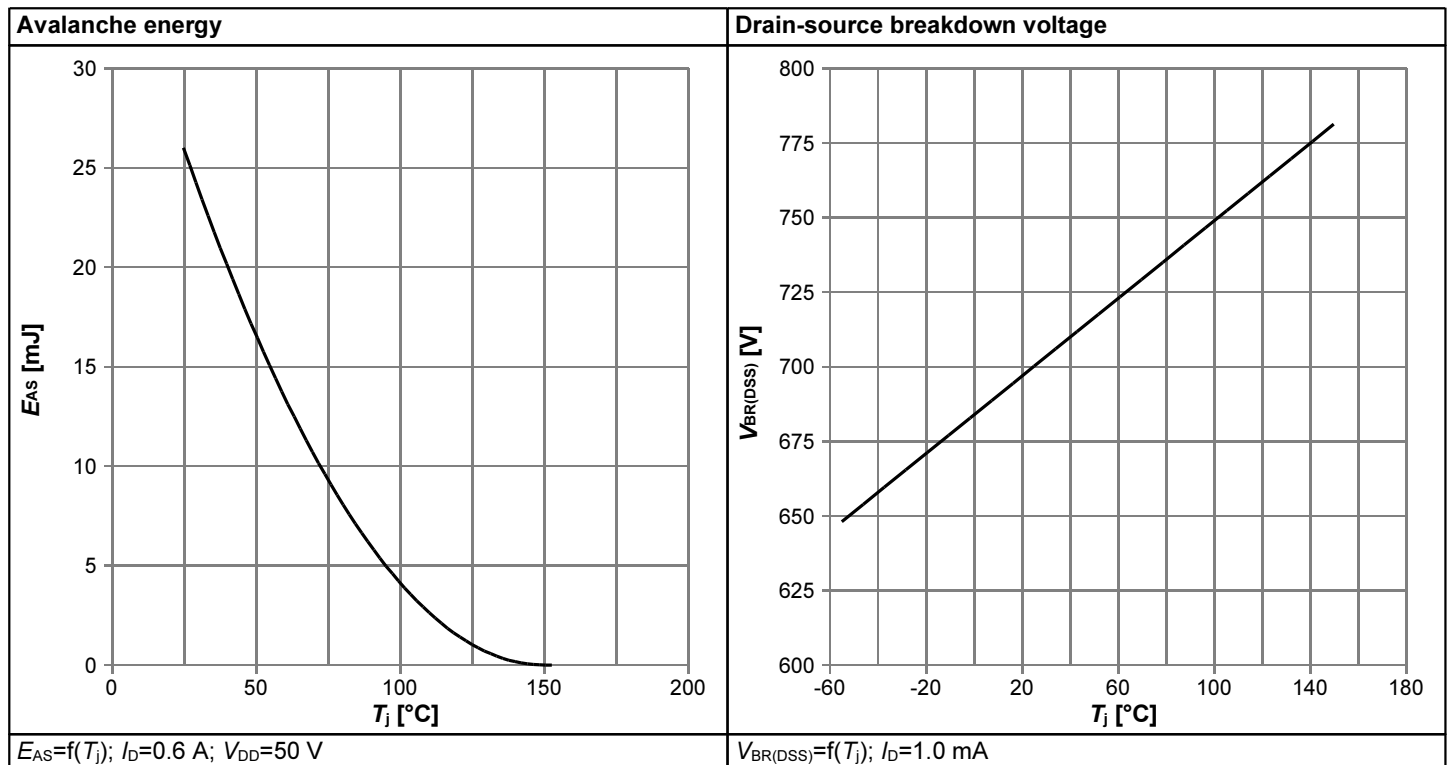


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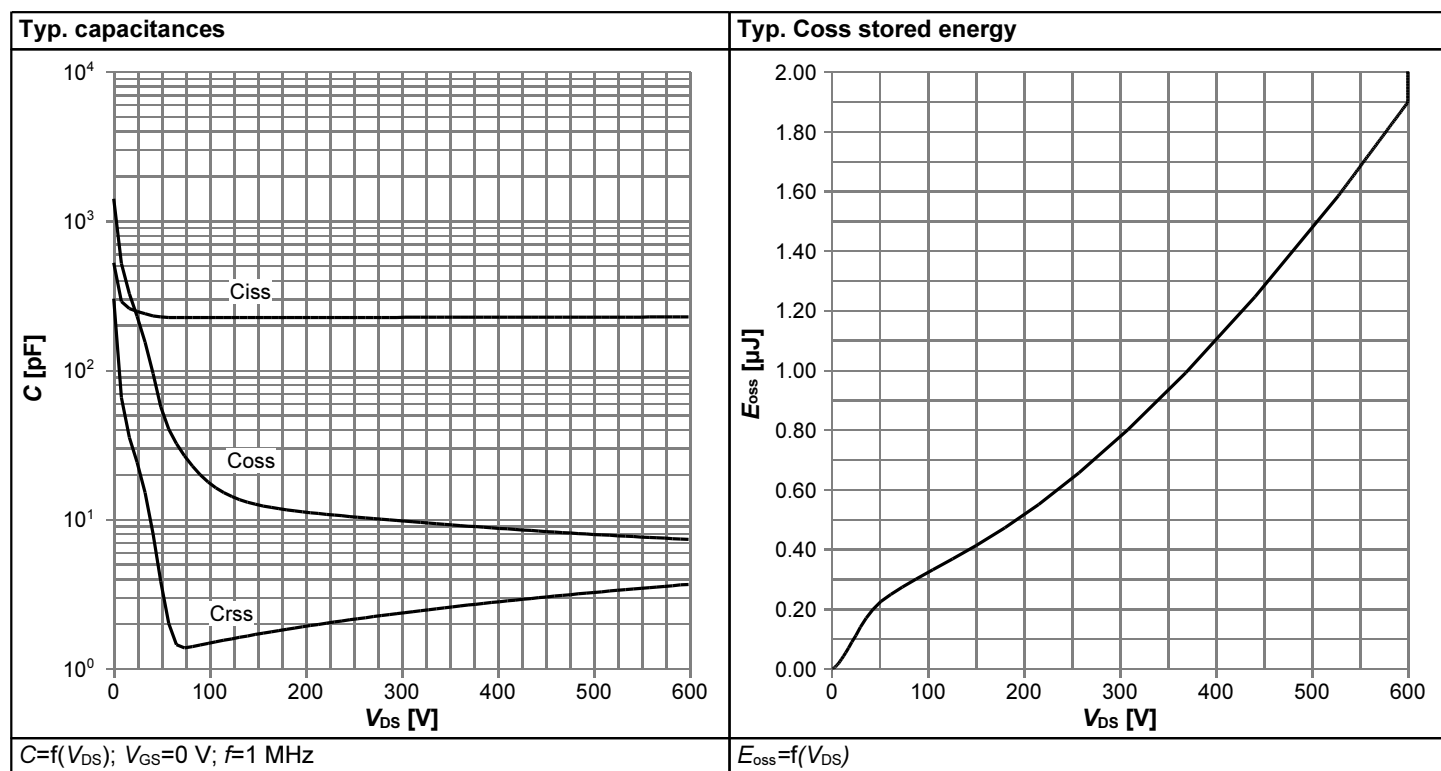
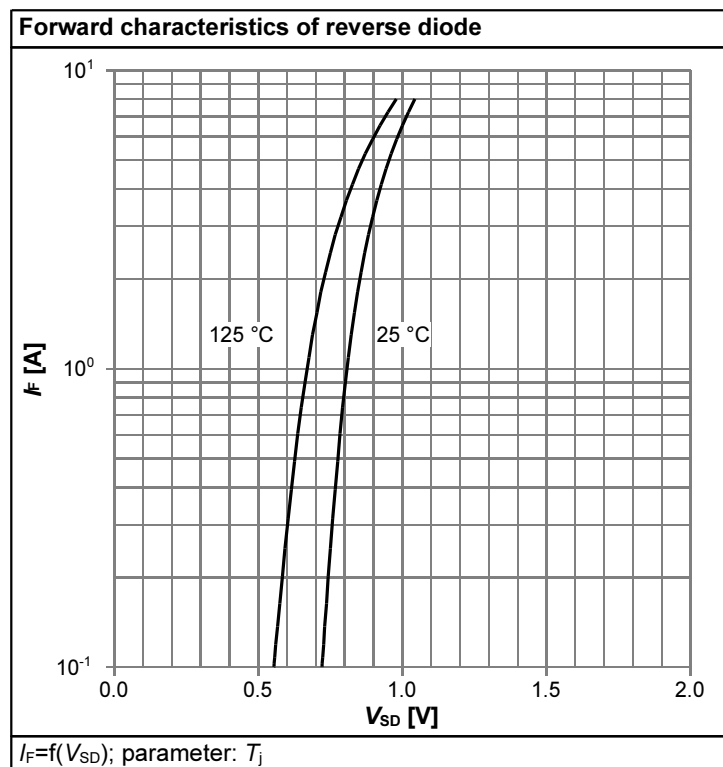
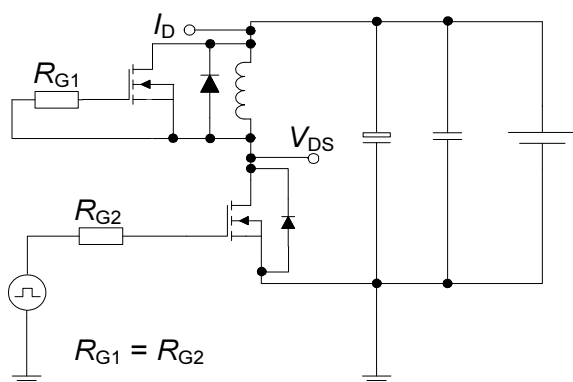
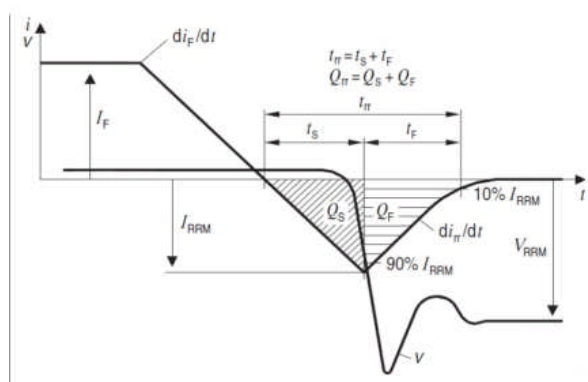


Table 15

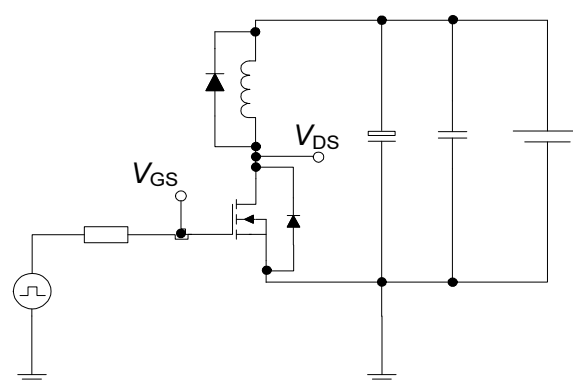
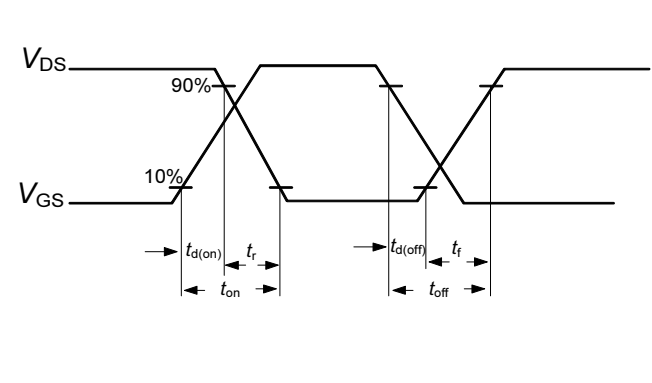


## 6 Test Circuits

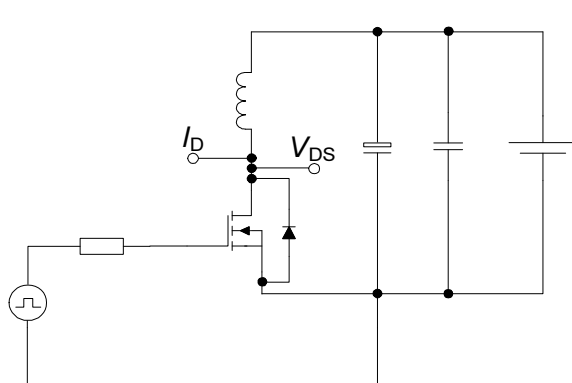
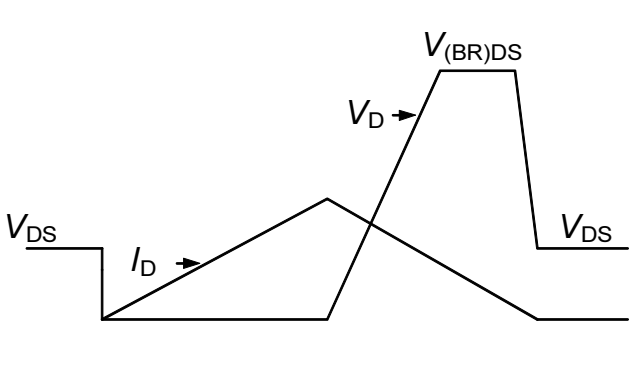
**Table 16 Diode characteristics**

Test circuit for diode characteristics	Diode recovery waveform
	

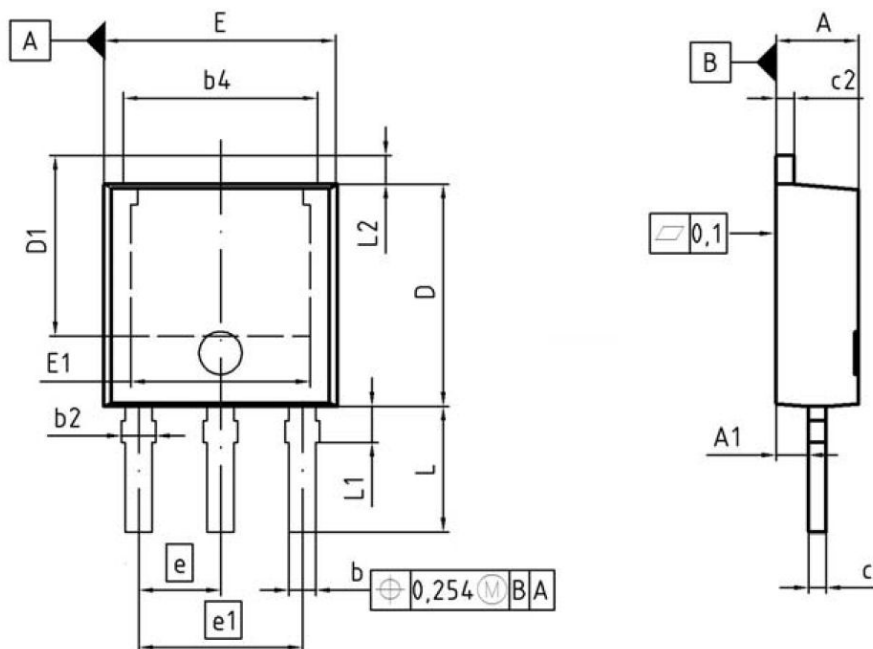
**Table 17 Switching times**

Switching times test circuit for inductive load	Switching times waveform
	

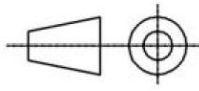
**Table 18 Unclamped inductive**

Unclamped inductive load test circuit	Unclamped inductive waveform
	

## 7 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.39	0.086	0.094
A1	0.80	1.14	0.031	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.58	0.018	0.023
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.44	0.198	0.214
E	6.35	6.73	0.250	0.265
E1	4.90	5.10	0.193	0.201
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	3.30	3.50	0.130	0.138
L1	0.90	1.10	0.035	0.043
L2	0.90	1.10	0.035	0.043

DOCUMENT NO. Z8B00003329
SCALE 0 2.0 4mm
EUROPEAN PROJECTION 
ISSUE DATE 05-07-2012
REVISION 04

**Figure 1 Outline PG-TO 251, dimensions in mm/inches**

## 8 Appendix A

### Table 19 Related Links

- IFX CoolMOS Webpage: [www.infineon.com](http://www.infineon.com)
- IFX Design Tools: [www.infineon.com](http://www.infineon.com)

## Revision History

SS05N70

**Revision: 2012-11-30, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2012-11-30	Release of final datasheet

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